Silicon NPN Power Transistors 2SD762 2SD762A

DESCRIPTION

- With TO-220C package
- Wide area of safe operation

APPLICATIONS

- For audio freuqency power amplifier applications

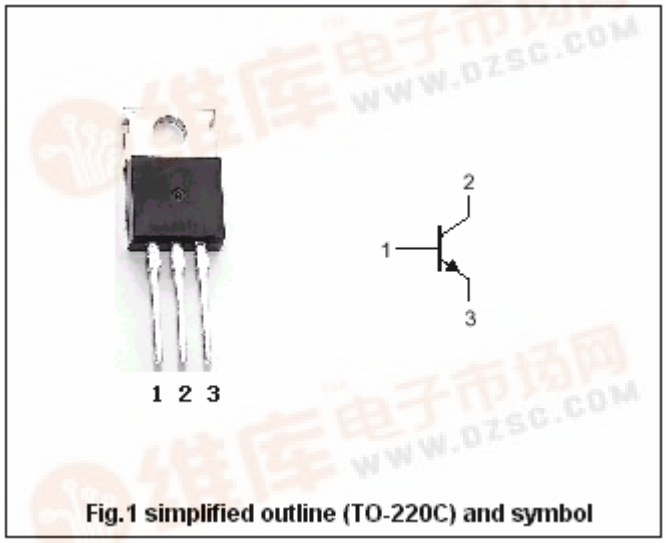

Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SD762	Open emitter	60	V
		2SD762A		80	
V_{CEO}	Collector-emitter voltage	2SD762	Open base	60	V
		2SD762A		80	
V_{EBO}	Emitter-base voltage		Open collector	8	V
I_C	Collector current			4	A
I_{CM}	Collector current-peak			6	A
I_B	Base current			1	A
P_C	Collector power dissipation		T_C=25℃	30	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

Silicon NPN Power Transistors 2SD762 2SD762A

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2SD762	I_C=0.2A; L=25mH	60			V
		2SD762A		80			
V_{CEsat}	Collector-emitter saturation voltage		I_C=2 A;I_B=0.4 A			1.0	V
V_{BE}	Base-emitter on voltage		I_C=1A ; V_{CE}=3V			1.2	V
I_{CBO}	Collector cut-off current		V_{CB}=50V; I_E=0			30	μA
I_{EBO}	Emitter cut-off current		V_{EB}=8V; I_C=0			1	mA
h_{FE-1}	DC current gain		I_C=0.1A ; V_{CE}=3V	40			
h_{FE-2}	DC current gain		I_C=1A ; V_{CE}=3V	30		160	

◆ **h_{FE-2} classifications**

Q	P	O
30-60	50-100	80-160

Silicon NPN Power Transistors 2SD762 2SD762A

PACKAGE OUTLINE

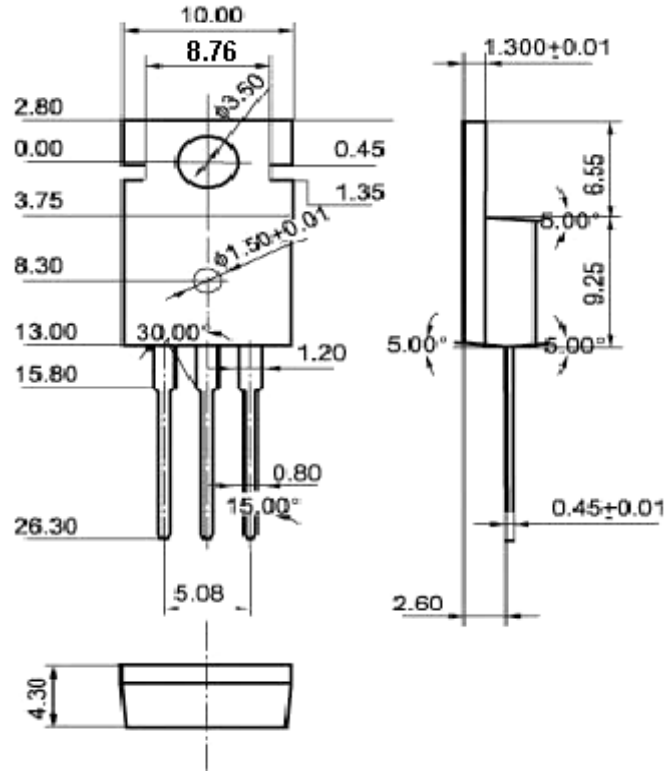

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)